



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	73mΩ @ V _{GS} = 10V	3.3A
30V	110mΩ @ V _{GS} = 4.5V	2.7A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- General Purpose Interfacing Switch
- **Power Management Functions**
- **Boost Application**
- Analog Switch

Features and Benefits

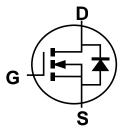
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

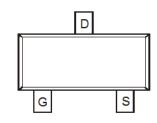
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.027 grams (Approximate)







Equivalent Circuit



Top View

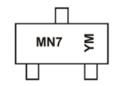
Ordering Information (Note 5)

-		
Part Number	Case	Packaging
DMN3110SQ-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



MN7 = Product Type Marking Code Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2007	~	2018	2019	202	0 20	21 2	022	2023	2024	2025	2026
Code	J	~	F	G	Н			J	K	L	М	N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	30	V	
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	2.5 2.0	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	3.3 2.7	А
Continuous Drain Current (Note 7) V _{GS} = 10V	t≦10sec	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	3.8 3.1	А
Continuous Drain Current (Note 7) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	2.7 2.1	А
Pulsed Drain Current (Note 8)			I _{DM}	25	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	0.74	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	173.4	°C/W
Total Power Dissipation (Note 7)	P_{D}	1.3	W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ heta JA}$	99.1	°C/W
Total Power Dissipation (Note 7) t≦10sec	P_{D}	1.8	W
Thermal Resistance, Junction to Ambient (Note 7) t≦10sec	$R_{ heta JA}$	72	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C

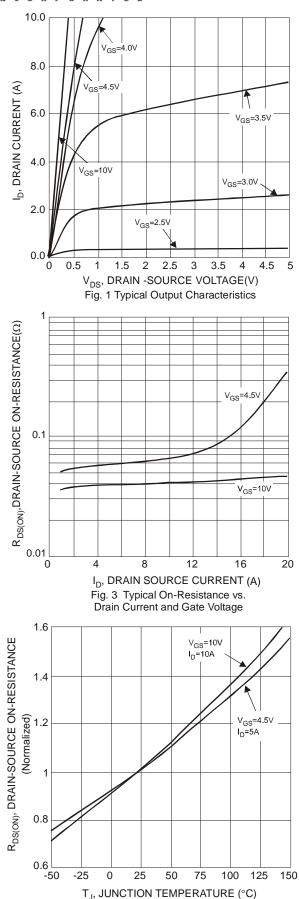
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symb	ool Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)	•					
Drain-Source Breakdown Voltage	BVDs	SS 30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current @T _C = +	+25°C I _{DSS}	3 -	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GS}	3 -	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(1}	_{TH)} 1.0	-	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance		-	54	73	mΩ	$V_{GS} = 10V, I_D = 3.1A$
Static Drain-Source On-Resistance	R _{DS(C}	ON) -	88	110	11122	$V_{GS} = 4.5V, I_D = 2A$
Forward Transfer Admittance	Y _{fs}	-	4.8	-	mS	$V_{DS} = 10V, I_D = 3.1A$
Diode Forward Voltage (Note 7)	V _{SE}	, -	0.75	1.0	V	$V_{GS} = 0V$, $I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	-	305.8	-	pF	45)/)/
Output Capacitance		s -	39.9	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	39.5	-	pF	T = 1.0WHZ
Gate Resistance	R _g	-	1.4	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	4.1	-	nC	
Total Gate Charge (V _{GS} = 10V)	Qg	-	8.6	-	nC	V 40V I 3A
Gate-Source Charge	Qgs	-	1.2	-	nC	$V_{DS} = 10V, I_{D} = 3A$
Gate-Drain Charge	Qgo		1.5	-	nC	
Turn-On Delay Time	t _{D(Of}	- ا	2.6	-	ns	
Turn-On Rise Time	t _R	-	4.6	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OF}	F) -	13.1	-	ns	$R_L = 47\Omega$, $R_G = 3\Omega$
Turn-Off Fall Time		-	2.5	-	ns	

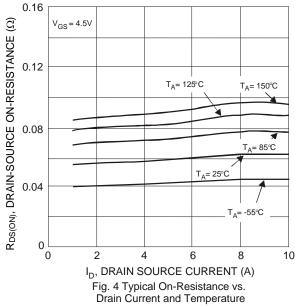
Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, on 1inch square copper plate.
 8. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.





T_A = 150°C $T_A = 125$ °C $T_A = 125$ °C $T_A = 25$ °C $T_A = 35$ °C



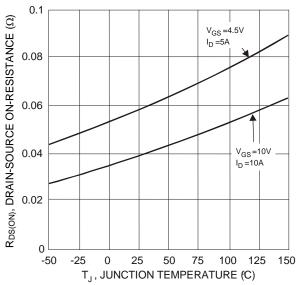


Fig. 5 On-Resistance Variation with Temperature



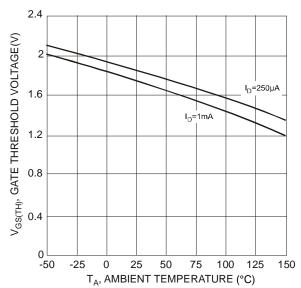
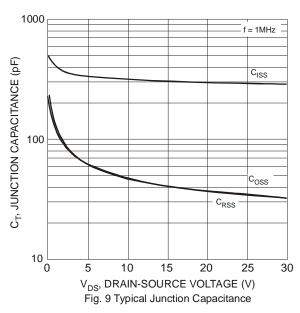
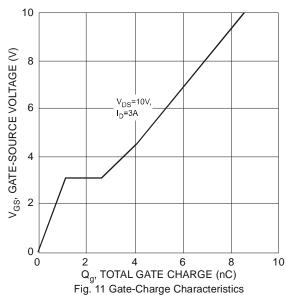
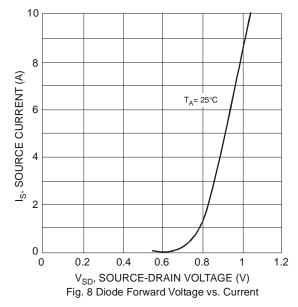
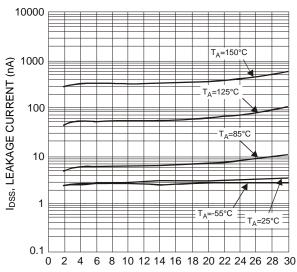


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



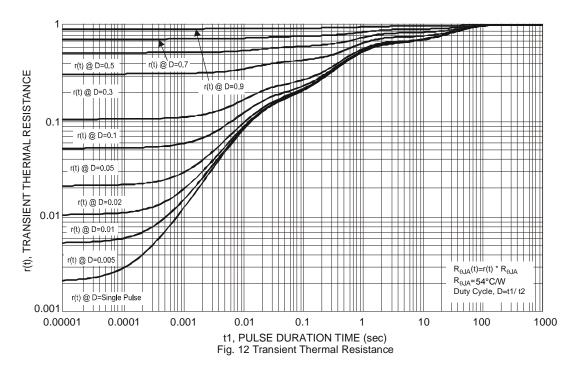






 $\label{eq:VDS} V_{DS}, \, \text{DRAIN-SOURCE VOLTAGE(V)}$ Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

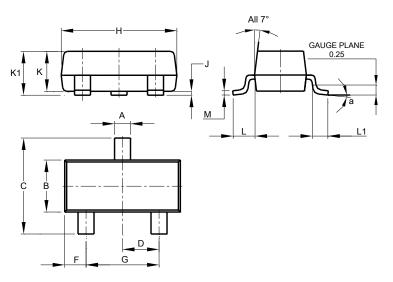




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



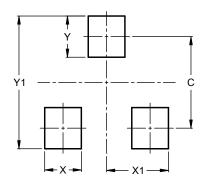
SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

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